TEXAS INSTRUMENTS

Data sheet acquired from Harris Semiconductor
SCHS188

January 1998

CD74HC534, CD74HCT534, CD74HC564, CD74HCT564

High Speed CMOS Logic Octal D-Type Flip-Flop, Three-State Inverting Positive-Edge Triggered

Features

- **Buffered Inputs**
- **Common Three-State Output-Enable Control**
- **Three-State Outputs**
- **Bus Line Driving Capability**
- **Typical Propagation Delay = 13ns at V_{CC} = 5V, C_L = 15pF, T_A = 25°C (Clock to Output)**
- **Fanout (Over Temperature Range)**
  - **Standard Outputs . . . . . 10 LSTTL Loads**
  - **Bus Driver Outputs . . . . . 15 LSTTL Loads**
- **Wide Operating Temperature Range . . . -55°C to 125°C**
- **Balanced Propagation Delay and Transition Times**
- **Significant Power Reduction Compared to LSTTL Logic ICs**
- **HC Types**
  - **2V to 6V Operation**
  - **High Noise Immunity: N_{IL} = 30%, N_{IH} = 30% of V_{CC} at V_{CC} = 5V**
- **HCT Types**
  - **4.5V to 5.5V Operation**
  - **Direct LSTTL Input Logic Compatibility, V_{IL}= 0.8V (Max), V_{IH} = 2V (Min)**
  - **CMOS Input Compatibility, $I_I \leq 1\mu A$ at V_{OL}, V_{OH}**

Description

The Harris CD74HC534, CD74HCT534, CD74HC564 and CD74HCT564 are high speed Octal D-Type Flip-Flops manufactured with silicon gate CMOS technology. They possess the low power consumption of standard CMOS integrated circuits, as well as the ability to drive 15 LSTTL loads. Due to the large output drive capability and the three-state feature, these devices are ideally suited for interfacing with bus lines in a bus organized system. The two types are functionally identical and differ only in their pinout arrangements.

The CD74HC534, CD74HCT534, CD74HC564 and CD74HCT564 are positive edge triggered flip-flops. Data at the D inputs, meeting the setup and hold time requirements, are inverted and transferred to the Q outputs on the positive going transition of the CLOCK input. When a high logic level is applied to the OUTPUT ENABLE input, all outputs go to a high impedance state, regardless of what signals are present at the other inputs and the state of the storage elements.

The CD74HCT logic family is speed, function, and pin compatible with the standard 74LS logic family.

Ordering Information

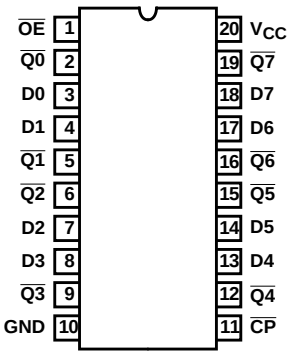
PART NUMBER	TEMP. RANGE (°C)	PACKAGE	PKG. NO.
CD74HC534E	-55 to 125	20 Ld PDIP	E20.3
CD74HCT534E	-55 to 125	20 Ld PDIP	E20.3
CD74HC564E	-55 to 125	20 Ld PDIP	E20.3
CD74HCT564E	-55 to 125	20 Ld PDIP	E20.3
CD74HC564M	-55 to 125	20 Ld SOIC	M20.3
CD74HCT564M	-55 to 125	20 Ld SOIC	M20.3

NOTES:

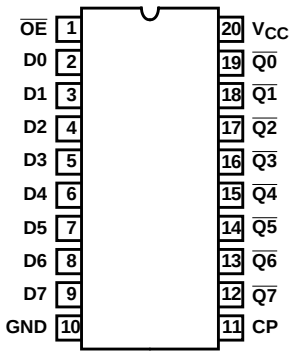
1. When ordering, use the entire part number. Add the suffix 96 to obtain the variant in the tape and reel.
2. Wafer and die for this part number is available which meets all electrical specifications. Please contact your local sales office or Harris customer service for ordering information.

Pinouts

CD74HC534, CD74HCT534 (PDIP)
TOP VIEW



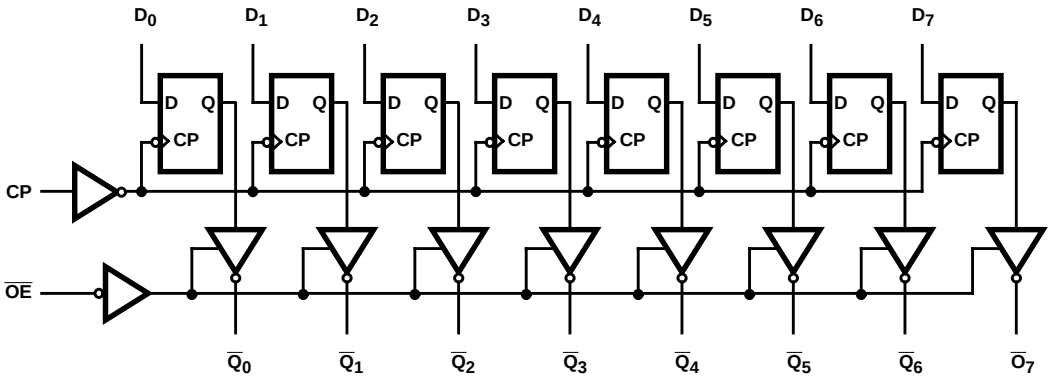
CD74HC564, CD74HCT564 (PDIP, SOIC)
TOP VIEW



CAUTION: These devices are sensitive to electrostatic discharge. Users should follow proper IC Handling Procedures.

File Number **1640.1**

Functional Diagram



TRUTH TABLE

INPUTS			OUTPUT
$\overline{OE}$	CP	Dn	$\overline{Qn}$
L	↑	H	L
L	↑	L	H
L	L	X	No Change
H	X	X	Z

NOTE:
H = High Level (Steady State)
L = Low Level (Steady State)
X = Don't Care
↑ = Transition from Low to High Level
Z = High Impedance State

Absolute Maximum Ratings

DC Supply Voltage, V_{CC} . . . . . -0.5V to 7V
DC Input Diode Current, I_{IK}
For V_I < -0.5V or V_I > V_{CC} + 0.5V . . . . . ±20mA
DC Output Diode Current, I_{OK}
For V_O < -0.5V or V_O > V_{CC} + 0.5V . . . . . ±20mA
DC Drain Current, per Output, I_O
For -0.5V < V_O < V_{CC} + 0.5V . . . . . ±35mA
DC Output Source or Sink Current per Output Pin, I_O
For V_O > -0.5V or V_O < V_{CC} + 0.5V . . . . . ±25mA
DC V_{CC} or Ground Current, I_{CC} . . . . . ±50mA

Operating Conditions

Temperature Range, T_A . . . . . -55°C to 125°C
Supply Voltage Range, V_{CC}
HC Types . . . . . 2V to 6V
HCT Types . . . . . 4.5V to 5.5V
DC Input or Output Voltage, V_I, V_O . . . . . 0V to V_{CC}
Input Rise and Fall Time
2V . . . . . 1000ns (Max)
4.5V. . . . . 500ns (Max)
6V . . . . . 400ns (Max)

Thermal Information

Thermal Resistance (Typical, Note 3)	θ_{JA} (°C/W)
PDIP Package	125
SOIC Package	120

Maximum Junction Temperature . . . . . 150°C
Maximum Storage Temperature Range . . . . . -65°C to 150°C
Maximum Lead Temperature (Soldering 10s) . . . . . 300°C
(SOIC - Lead Tips Only)

CAUTION: Stresses above those listed in "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress only rating and operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied.

NOTE:

3. θ_{JA} is measured with the component mounted on an evaluation PC board in free air.

DC Electrical Specifications

PARAMETER	SYMBOL	TEST CONDITIONS		V_{CC} (V)	25°C			-40°C TO 85°C		-55°C TO 125°C		UNITS
		V_I (V)	I_O (mA)		MIN	TYP	MAX	MIN	MAX	MIN	MAX	
HC TYPES												
High Level Input Voltage	V_{IH}	-	-	2	1.5	-	-	1.5	-	1.5	-	V
				4.5	3.15	-	-	3.15	-	3.15	-	V
				6	4.2	-	-	4.2	-	4.2	-	V
Low Level Input Voltage	V_{IL}	-	-	2	-	-	0.5	-	0.5	-	0.5	V
				4.5	-	-	1.35	-	1.35	-	1.35	V
				6	-	-	1.8	-	1.8	-	1.8	V
High Level Output Voltage CMOS Loads	V_{OH}	V_{IH} or V_{IL}	-0.02	2	1.9	-	-	1.9	-	1.9	-	V
			-0.02	4.5	4.4	-	-	4.4	-	4.4	-	V
			-0.02	6	5.9	-	-	5.9	-	5.9	-	V
High Level Output Voltage TTL Loads			-	-	-	-	-	-	-	-	-	V
			-6	4.5	3.98	-	-	3.84	-	3.7	-	V
			-7.8	6	5.48	-	-	5.34	-	5.2	-	V
Low Level Output Voltage CMOS Loads	V_{OL}	V_{IH} or V_{IL}	0.02	2	-	-	0.1	-	0.1	-	0.1	V
			0.02	4.5	-	-	0.1	-	0.1	-	0.1	V
			0.02	6	-	-	0.1	-	0.1	-	0.1	V
Low Level Output Voltage TTL Loads			-	-	-	-	-	-	-	-	-	V
			6	4.5	-	-	0.26	-	0.33	-	0.4	V
			7.8	6	-	-	0.26	-	0.33	-	0.4	V
Input Leakage Current	I_I	V_{CC} or GND	-	6	-	-	±0.1	-	±1	-	±1	µA

DC Electrical Specifications (Continued)

PARAMETER	SYMBOL	TEST CONDITIONS		V_{CC} (V)	25°C			-40°C TO 85°C		-55°C TO 125°C		UNITS
		V_I (V)	I_O (mA)		MIN	TYP	MAX	MIN	MAX	MIN	MAX	
Quiescent Device Current	I_{CC}	V_{CC} or GND	0	6	-	-	8	-	80	-	160	µA
Three- State Leakage Current	V_{IL} or V_{IH}	$V_O = V_{CC}$ or GND	-	6	-	-	±0.5	-	±5.0	-	±10	µA
HCT TYPES												
High Level Input Voltage	V_{IH}	-	-	4.5 to 5.5	2	-	-	2	-	2	-	V
Low Level Input Voltage	V_{IL}	-	-	4.5 to 5.5	-	-	0.8	-	0.8	-	0.8	V
High Level Output Voltage CMOS Loads	V_{OH}	V_{IH} or V_{IL}	-0.02	4.5	4.4	-	-	4.4	-	4.4	-	V
High Level Output Voltage TTL Loads			-6	4.5	3.98	-	-	3.84	-	3.7	-	V
Low Level Output Voltage CMOS Loads	V_{OL}	V_{IH} or V_{IL}	0.02	4.5	-	-	0.1	-	0.1	-	0.1	V
Low Level Output Voltage TTL Loads			6	4.5	-	-	0.26	-	0.33	-	0.4	V
Input Leakage Current	I_I	V_{CC} and GND	0	5.5	-		±0.1	-	±1	-	±1	µA
Quiescent Device Current	I_{CC}	V_{CC} or GND	0	5.5	-	-	8	-	80	-	160	µA
Three- State Leakage Current	V_{IL} or V_{IH}	$V_O = V_{CC}$ or GND	-	5.5	-	-	±0.5	-	±5.0	-	±10	µA
Additional Quiescent Device Current Per Input Pin: 1 Unit Load	ΔI_{CC}	V_{CC} -2.1	-	4.5 to 5.5	-	100	360	-	450	-	490	µA

NOTE: For dual-supply systems theoretical worst case (V_I = 2.4V, V_{CC} = 5.5V) specification is 1.8mA.

HCT Input Loading Table

INPUT	UNIT LOADS
D0 - D7	0.15
CP	0.30
$\overline{OE}$	0.55

NOTE: Unit load is ΔI_{CC} limit specific in DC Electrical Specifications Table, e.g., 360µA max. at 25°C.

Prerequisite for Switching Specifications

PARAMETER	SYMBOL	V_{CC} (V)	25°C			-40°C TO 85°C			-55°C TO 125°C			UNITS
			MIN	TYP	MAX	MIN	TYP	MAX	MIN	TYP	MAX	
HC TYPES												
Maximum Clock Frequency	f_{MAX}	2	6	-	-	5	-	-	4	-	-	MHz
		4.5	30	-	-	25	-	-	20	-	-	MHz
		6	35	-	-	29	-	-	23	-	-	MHz
Clock Pulse Width	t_W	2	80	-	-	100	-	-	120	-	-	ns
		4.5	16	-	-	20	-	-	24	-	-	ns
		6	14	-	-	17	-	-	20	-	-	ns
Setup Time Data to Clock	t_{SU}	2	60	-	-	75	-	-	90	-	-	ns
		4.5	12	-	-	15	-	-	18	-	-	ns
		6	10	-	-	13	-	-	15	-	-	ns
Hold Time Data to Clock	t_H	2	5	-	-	5	-	-	5	-	-	ns
		4.5	5	-	-	5	-	-	5	-	-	ns
		6	5	-	-	5	-	-	5	-	-	ns
HCT TYPES												
Maximum Clock Frequency	f_{MAX}	4.5	25	-	-	20	-	-	16	-	-	MHz
Clock Pulse Width	t_W	4.5	20	-	-	25	-	-	30	-	-	ns
Setup Time Data to Clock	t_{SU}	4.5	20	-	-	25	-	-	30	-	-	ns
Hold Time Data to Clock (534)	t_H	4.5	5	-	-	5	-	-	5	-	-	ns
Hold Time Data to Clock (564)	t_H	4.5	3	-	-	3	-	-	3	-	-	ns

Switching Specifications C_L = 50pF, Input t_r, t_f = 6ns

PARAMETER	SYMBOL	TEST CONDITIONS	V_{CC} (V)	25°C			-40°C TO 85°C		-55°C TO 125°C		UNITS
				MIN	TYP	MAX	MIN	MAX	MIN	MAX	
HC TYPES											
Propagation Delay Clock to Output	t_{PLH}, t_{PHL}	C_L = 50pF	2	-	-	165	-	205	-	250	ns
			4.5	-	-	33	-	41	-	50	ns
		C_L = 15pF	5	-	13	-	-	-	-	-	ns
		C_L = 50pF	6	-	-	28	-	35	-	43	ns
Output Disable to Q (534)	t_{PLZ}, t_{PHZ}	C_L = 50pF	2	-	-	150	-	190	-	225	ns
			4.5	-	-	30	-	38	-	45	ns
		C_L = 15pF	5	-	12	-	-	-	-	-	ns
		C_L = 50pF	6	-	-	26	-	33	-	38	ns

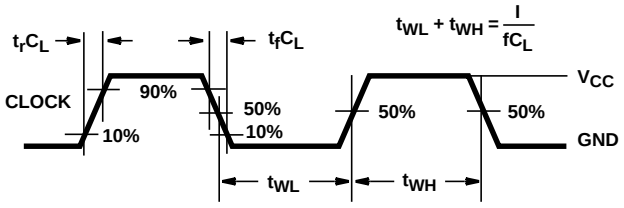
Switching Specifications C_L = 50pF, Input t_r, t_f = 6ns **(Continued)**

PARAMETER	SYMBOL	TEST CONDITIONS	V_{CC} (V)	25°C			-40°C TO 85°C		-55°C TO 125°C		UNITS
				MIN	TYP	MAX	MIN	MAX	MIN	MAX	
Output Disable to Q (564)	t_{PLZ}, t_{PHZ}	C_L = 50pF	2	-	-	135	-	170	-	205	ns
			4.5	-	-	27	-	34	-	41	ns
		C_L = 15pF	5	-	12	-	-	-	-	-	ns
		C_L = 50pF	6	-	-	23	-	29	-	35	ns
Output Enable to Q	t_{PZL}, t_{PZH}	C_L = 50pF	2	-	-	150	-	190	-	225	ns
			4.5	-	-	30	-	38	-	45	ns
		C_L = 15pF	5	-	12	-	-	-	-	-	ns
		C_L = 50pF	6	-	-	26	-	33	-	38	ns
Maximum Clock Frequency	f_{MAX}	C_L = 15pF	5	-	60	-	-	-	-	-	MHz
Output Transition Time	t_{THL}, t_{TLH}	C_L = 50pF	2	-	-	60	-	75	-	90	ns
			4.5	-	-	12	-	15	-	18	ns
			6	-	-	10	-	13	-	15	ns
Input Capacitance	C_I	C_L = 50pF	-	10	-	10	-	10	-	10	pF
Three-State Output Capacitance	C_O	-	-	20	-	20	-	20	-	20	pF
Power Dissipation Capacitance (Notes 4, 5)	C_{PD}	-	5	-	32	-	-	-	-	-	pF
HCT TYPES											
Propagation Delay Clock to Output	t_{PHL}, t_{PLH}	C_L = 50pF	4.5	-	-	35	-	44	-	53	ns
		C_L = 15pF	5	-	14	-	-	-	-	-	ns
Output Disable to Q	t_{PLZ}, t_{PHZ}	C_L = 50pF	4.5	-	-	30	-	38	-	45	ns
		C_L = 15pF	5	-	12	-	-	-	-	-	ns
Output Enable to Q	t_{PZL}, t_{PZH}	C_L = 50pF	4.5	-	-	35	-	44	-	53	ns
		C_L = 15pF	5	-	14	-	-	-	-	-	ns
Maximum Clock Frequency	f_{MAX}	C_L = 15pF	5	-	50	-	-	-	-	-	MHz
Output Transition Time	t_{TLH}, t_{THL}	C_L = 50pF	4.5	-	-	12	-	15	-	18	ns
Input Capacitance	C_I	C_L = 50pF	-	10	-	10	-	10	-	10	pF
Three-State Output Capacitance	C_O	-	-	20	-	20	-	20	-	20	pF
Power Dissipation Capacitance (Notes 4, 5)	C_{PD}	-	5	-	36	-	-	-	-	-	pF

NOTES:

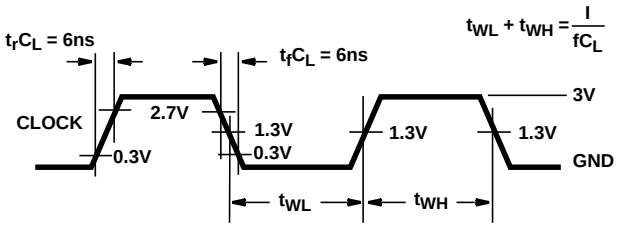
4. C_{PD} is used to determine the dynamic power consumption, per package.
5. $P_D = C_{PD} V_{CC}^2 f_i + \Sigma C_L V_{CC}^2 f_O$ where f_i = Input Frequency, f_O = Output Frequency, C_L = Output Load Capacitance, V_{CC} = Supply Voltage.

Test Circuits and Waveforms



NOTE: Outputs should be switching from 10% V_{CC} to 90% V_{CC} in accordance with device truth table. For f_{MAX}, input duty cycle = 50%.

FIGURE 1. HC CLOCK PULSE RISE AND FALL TIMES AND PULSE WIDTH



NOTE: Outputs should be switching from 10% V_{CC} to 90% V_{CC} in accordance with device truth table. For f_{MAX}, input duty cycle = 50%.

FIGURE 2. HCT CLOCK PULSE RISE AND FALL TIMES AND PULSE WIDTH

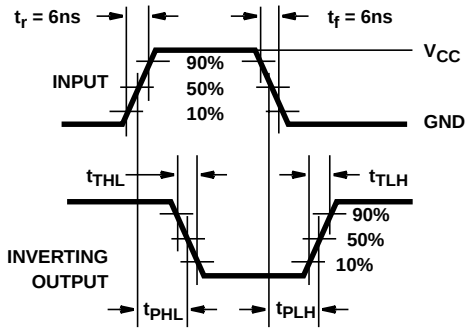


FIGURE 3. HC TRANSITION TIMES AND PROPAGATION DELAY TIMES, COMBINATION LOGIC

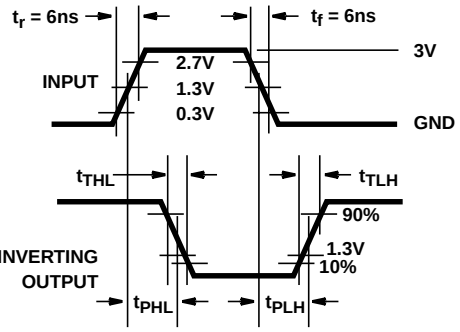


FIGURE 4. HCT TRANSITION TIMES AND PROPAGATION DELAY TIMES, COMBINATION LOGIC

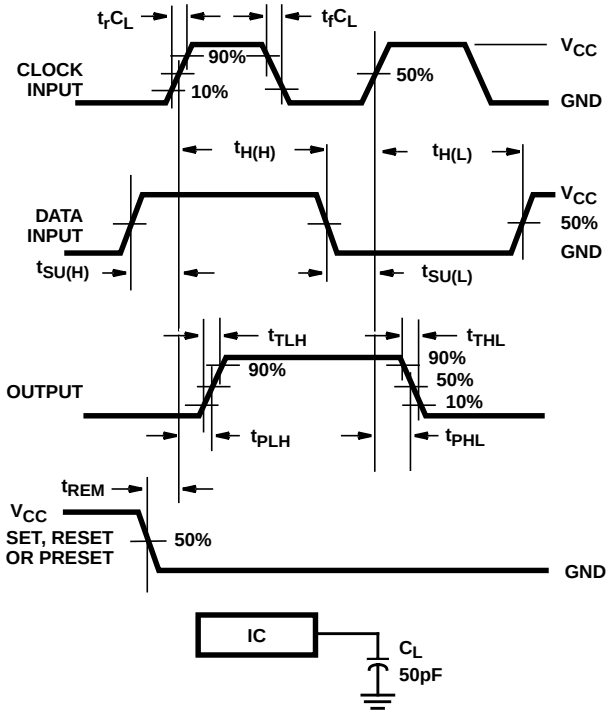


FIGURE 5. HC SETUP TIMES, HOLD TIMES, REMOVAL TIME, AND PROPAGATION DELAY TIMES FOR EDGE TRIGGERED SEQUENTIAL LOGIC CIRCUITS

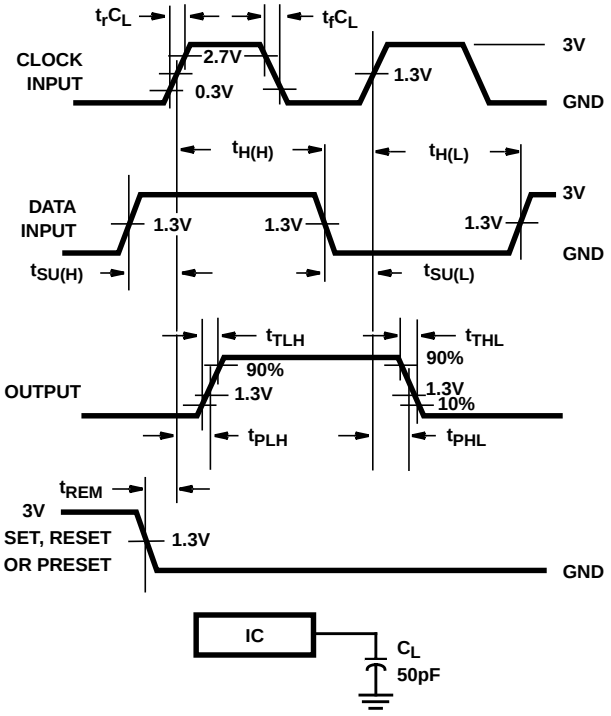


FIGURE 6. HCT SETUP TIMES, HOLD TIMES, REMOVAL TIME, AND PROPAGATION DELAY TIMES FOR EDGE TRIGGERED SEQUENTIAL LOGIC CIRCUITS

Test Circuits and Waveforms (Continued)

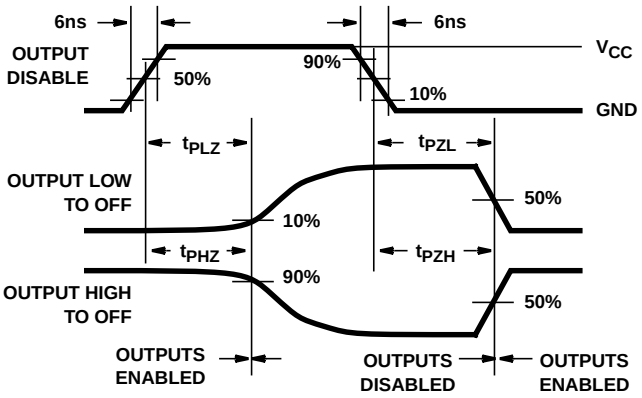


FIGURE 7. HC THREE-STATE PROPAGATION DELAY WAVEFORM

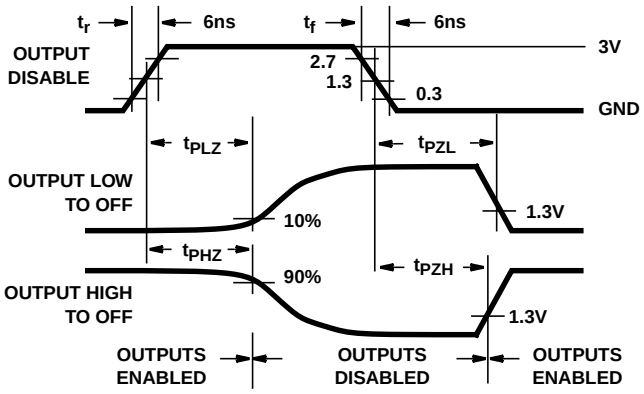
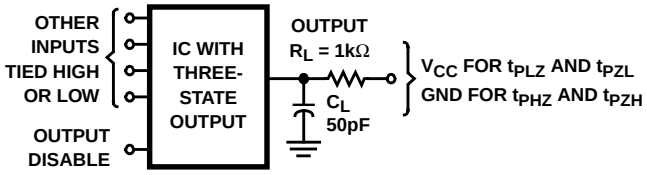


FIGURE 8. HCT THREE-STATE PROPAGATION DELAY WAVEFORM



NOTE: Open drain waveforms t_{PLZ} and t_{PZL} are the same as those for three-state shown on the left. The test circuit is Output R_L = 1kΩ to V_{CC}, C_L = 50pF.

FIGURE 9. HC AND HCT THREE-STATE PROPAGATION DELAY TEST CIRCUIT

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